Chapter 2 Bipolar Junction Transistor (BJT) Biasing

One mark questions (knowledge)

- 1. Define operating point.
- 2. What is DC load line?
- 3. Define quiescent point.
- 4. What is leakage current in BJT?
- 5. Write the relation between $I_{\mbox{\tiny CBO}}$ and $I_{\mbox{\tiny CEO}}.$
- 6. What is thermal run away?
- 7. Define stability factor in BJT.
- 8. What is heat sink?

One mark questions (understanding)

- 1. What is meant by transistor biasing?
- 2. Why transistor is called as a current controlled device?
- 3. Name the two end points of the DC load line.
- 4. What is the value of V_{CE} at saturation point?
- 5. What is the value of I_c at cut off point?
- 6. Where should the Q point be located for the transistor to be operated as an amplifier?
- 7. Write the expression for DC load line of a transistor in CE configuration?
- 8. For the BJT to work as a closed switch where should the operating point be located on the DC load line?
- 9. For the BJT to work as an open switch where should the operating point be located on the DC load line?
- 10. Mention the transistor parameter that is temperature dependent.
- 11. Mention any one leakage current in a transistor.
- 12. Name any one biasing method for a transistor.
- 13. Name the biasing circuit which gives excellent stabilization.

Two mark questions (knowledge)

- 1. What are the biasing conditions for a transistor to be used as an amplifier?
- 2. Mention any two types of biasing methods.
- 3. What is leakage current? Mention different types of leakage currents.

Two mark questions (understanding)

- 1. What is the need for biasing a transistor?
- 2. Write the advantages of voltage divider bias circuit.
- 3. What is a heat sink? Mention its importance.

Two mark questions (skill)

- 1. Sketch the transistor output characteristics in CE mode. Indicate different regions of the characteristics.
- 2. Draw the biasing arrangement for an npn transistor in CE configuration with two sources.
- 3. Draw the DC load line on the output characteristics of a CE amplifier.

4. Draw the circuit diagram of a Voltage divider bias circuit.

Three mark questions (knowledge)

- 1. What is Q point? Explain its significance.
- 2. What is meant by stability factor? Mention the factors affecting it.

Three mark questions (understanding)

- 1. What is transistor biasing? Explain the need for biasing.
- 2. Derive an expression for the DC load line for a transistor in CE mode biased with two sources.
- 3. What is voltage divider bias? Mention its advantages.
- 4. Explain the leakage currents in CE and CB configurations.

Problems:

- 1. A transistor connected in CE mode in which collector supply is 8V and voltage drop across $R_c = 800\Omega$ connected in the collector circuit is 0.5V. If $\alpha = 0.96$ determine V_{CE} and I_B .
- 2. A transistor has β = 100 and I_{CBO} = 5µA when it is connected in a circuit as a CE stage with zero load resistance, the collector current I_C = 1mA. Calculate the values of I_B, I_E and α .
- 3. For the given parameters values of voltage divider biasing circuit, determine the end points of the dc load line and draw the DC load line $R_1=56K\Omega$, $R_2=10K\Omega$, $R_c=2.2K\Omega$, $R_E=1K\Omega$ and $V_{cc}=12V$.